The listing of claims will replace all prior versions, and listings, of claims in the application:

## **Listing of Claims:**

- 1. (Original) A light emitting device comprising:
- a thin film transistor on an insulating surface;
- an interlayer insulating film over the thin film transistor;
- an anode over the interlayer insulating film;
- a wiring electrically connected to the thin film transistor and the anode;
- a bank over the wiring and the anode;
- a first insulating film over the anode and the bank;
- an organic compound layer over the anode with the first insulating film interposed therebetween; and
  - a cathode over the organic compound layer.
  - 2. (Original) A light emitting device comprising:
  - a thin film transistor on an insulating surface;
  - an interlayer insulating film over the thin film transistor;
  - an anode over the interlayer insulating film;
  - a wiring electrically connected to the thin film transistor and the anode;
  - a bank over the wiring and the anode;
  - a first insulating film over the anode and the bank;
- an organic compound layer over the anode with the first insulating film interposed therebetween; and
  - a cathode over the organic compound layer,
  - wherein the first insulating film is formed from an organic resin film.

- 3. (Original) A light emitting device comprising:
- a thin film transistor on an insulating surface;
- an interlayer insulating film over the thin film transistor;
- an anode over the interlayer insulating film;
- a wiring electrically connected to the thin film transistor and the anode;
- a bank over the wiring and the anode;
- a first insulating film over the anode and the bank;
- an organic compound layer over the anode with the first insulating film interposed therebetween; and
  - a cathode over the organic compound layer, wherein the first insulating film is at a film thickness of 1 to 5nm.
  - 4. (Canceled)
  - 5. (Currently Amended) A light emitting device comprising:
  - a thin film transistor on an insulating surface;
  - an interlayer insulating film over the thin film transistor;
  - an anode over the interlayer insulating film;
  - a wiring electrically connected to the thin film transistor and the anode;
  - a bank over the wiring and the anode;
  - a first insulating film over the anode and the bank;
- an organic compound layer over the anode with the first insulating film interposed therebetween; and
  - a cathode over the organic compound layer.
  - wherein the anode is formed from indium [[thin]] <u>tin</u> oxide.
  - 6. (Currently Amended) A light emitting device comprising:
  - a thin film transistor on an insulating surface;

an interlayer insulating film over the thin film transistor;

an anode over the interlayer insulating film;

a wiring electrically connected to the thin film transistor and the anode;

a bank over the wiring and the anode;

a first insulating film over the anode and the bank;

an organic compound layer over the anode with the first insulating film interposed therebetween; and

a cathode over the organic compound [[layer.]] <u>layer;</u> wherein the first insulating film is formed from an organic resin film; wherein the first insulating film is at a film thickness of 1 to 5nm; and wherein the anode is formed from indium [[thin]] <u>tin</u> oxide.

- 7. (Original) A device according to claim 1, wherein an average surface roughness (Ra) of the anode is in a range of 0.9 nm or less.
- 8. (Original) A device according to claim 1, wherein an average surface roughness (Ra) of the anode is in a range of 0.85 nm or less.
- 9. (Original) A device according to claim 1, wherein the interlayer insulating film comprises at least one selected from the group consisting of a silicon oxide film, a silicon nitride oxide film and a silicon oxide nitride film.
  - 10. (Original) A device according to claim 1, wherein the bank is processed by a plasma; and

wherein the bank comprises a hardened film including at least an element selected from the group consisting of hydrogen, nitrogen, halocarbon, hydrogen fluoride, and noble gas.

11. (Original) A device according to claim 1,

wherein a second insulating film is formed over the interlayer insulating film; and wherein the second insulating film comprises at least one selected from the group consisting of a silicon nitride film and a diamond like carbon film.

12. (Original) A device according to claim 1,

wherein the light emitting device is in combination with an electric device; and wherein the electric device is one selected from the group consisting of a display, a digital still camera, a notebook type personal computer, a mobile computer, an image reproduction apparatus including a recording medium, a goggle type display, a video camera and a mobile phone.

- 13. (Original) A device according to claim 2, wherein an average surface roughness (Ra) of the anode is in a range of 0.9 nm or less.
- 14. (Original) A device according to claim 2, wherein an average surface roughness (Ra) of the anode is in a range of 0.85 nm or less.
- 15. (Original) A device according to claim 2, wherein the interlayer insulating film comprises at least one selected from the group consisting of a silicon oxide film, a silicon nitride oxide film and a silicon oxide nitride film.
  - 16. (Original) A device according to claim 2,

wherein the bank is processed by a plasma; and

wherein the bank comprises a hardened film including at least an element selected from the group consisting of hydrogen, nitrogen, halocarbon, hydrogen fluoride, and noble gas.

- 17. (Original) A device according to claim 2,
- wherein a second insulating film is formed over the interlayer insulating film; and wherein the second insulating film comprises at least one selected from the group consisting of a silicon nitride film and a diamond like carbon film.
- 18. (Original) A device according to claim 2, wherein the light emitting device is in combination with an electric device; and wherein the electric device is one selected from the group consisting of a display, a digital still camera, a notebook type personal computer, a mobile computer, an image reproduction apparatus including a recording medium, a goggle type display, a video camera and a mobile phone.
- 19. (Original) A device according to claim 3, wherein an average surface roughness (Ra) of the anode is in a range of 0.9 nm or less.
- 20. (Original) A device according to claim 3, wherein an average surface roughness (Ra) of the anode is in a range of 0.85 nm or less.
- 21. (Original) A device according to claim 3, wherein the interlayer insulating film comprises at least one selected from the group consisting of a silicon oxide film, a silicon nitride oxide film and a silicon oxide nitride film.
  - 22. (Original) A device according to claim 3,

wherein the bank is processed by a plasma; and

wherein the bank comprises a hardened film including at least an element selected from the group consisting of hydrogen, nitrogen, halocarbon, hydrogen fluoride, and noble gas.

23. (Original) A device according to claim 3,

wherein a second insulating film is formed over the interlayer insulating film; and wherein the second insulating film comprises at least one selected from the group consisting of a silicon nitride film and a diamond like carbon film.

24. (Original) A device according to claim 3,

wherein the light emitting device is in combination with an electric device; and wherein the electric device is one selected from the group consisting of a display, a digital still camera, a notebook type personal computer, a mobile computer, an image reproduction apparatus including a recording medium, a goggle type display, a video camera and a mobile phone.

## 25.-30. (Canceled)

- 31. (Original) A device according to claim 5, wherein an average surface roughness (Ra) of the anode is in a range of 0.9 nm or less.
- 32. (Original) A device according to claim 5, wherein an average surface roughness (Ra) of the anode is in a range of 0.85 nm or less.
- 33. (Original) A device according to claim 5, wherein the interlayer insulating film comprises at least one selected from the group consisting of a silicon oxide film, a silicon nitride oxide film and a silicon oxide nitride film.
  - 34. (Original) A device according to claim 5, wherein the bank is processed by a plasma; and

wherein the bank comprises a hardened film including at least an element selected from the group consisting of hydrogen, nitrogen, halocarbon, hydrogen fluoride, and noble gas.

35. (Original) A device according to claim 5,

wherein a second insulating film is formed over the interlayer insulating film; and wherein the second insulating film comprises at least one selected from the group consisting of a silicon nitride film and a diamond like carbon film.

36. (Original) A device according to claim 5,

wherein the light emitting device is in combination with an electric device; and wherein the electric device is one selected from the group consisting of a display, a digital still camera, a notebook type personal computer, a mobile computer, an image reproduction apparatus including a recording medium, a goggle type display, a video camera and a mobile phone.

- (Original) A device according to claim 6, wherein an average surface 37. roughness (Ra) of the anode is in a range of 0.9 nm or less.
- (Original) A device according to claim 6, wherein an average surface roughness (Ra) of the anode is in a range of 0.85 nm or less.
- 39. (Original) A device according to claim 6, wherein the interlayer insulating film comprises at least one selected from the group consisting of a silicon oxide film, a silicon nitride oxide film and a silicon oxide nitride film.
  - 40. (Original) A device according to claim 6, wherein the bank is processed by a plasma; and

wherein the bank comprises a hardened film including at least an element selected from the group consisting of hydrogen, nitrogen, halocarbon, hydrogen fluoride, and noble gas.

- 41. (Original) A device according to claim 6, wherein a second insulating film is formed over the interlayer insulating film; and wherein the second insulating film comprises at least one selected from the group consisting of a silicon nitride film and a diamond like carbon film.
- 42. (Original) A device according to claim 6, wherein the light emitting device is in combination with an electric device; and wherein the electric device is one selected from the group consisting of a display, a digital still camera, a notebook type personal computer, a mobile computer, an image reproduction apparatus including a recording medium, a goggle type display, a video camera and a mobile phone.
  - 43. (New) A device according to claim 1, wherein the bank is formed from a resin insulating film.
  - 44. (New) A device according to claim 2, wherein the bank is formed from a resin insulating film.
  - 45. (New) A device according to claim 3, wherein the bank is formed from a resin insulating film.
  - 46. (New) A device according to claim 5, wherein the bank is formed from a resin insulating film.

47. (New) A device according to claim 6, wherein the bank is formed from a resin insulating film.